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# **State-of-the-Art Program on Compound Semiconductors 46 (SOTAPOCS 46) -and- Processes at the Semiconductor/Solution Interface 2**

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 **Electronics and Photonics**

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Published by

**The Electrochemical Society**

65 South Main Street, Building D  
Pennington, NJ 08534-2839, USA

tel 609 737 1902

fax 609 737 2743

[www.electrochem.org](http://www.electrochem.org)

**ECS** transactions™

**Vol. 6 No. 2**

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Published by:  
The Electrochemical Society, Inc.  
65 South Main Street  
Pennington, New Jersey 08534-2839, USA  
Telephone 609.737.1902  
Fax 609.737.2743  
e-mail: [ecs@electrochem.org](mailto:ecs@electrochem.org)  
Web: [www.electrochem.org](http://www.electrochem.org)

978-1-56677-551-9

Printed in the United States of America

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**ECS Transactions, Volume 6, Issue 2**

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\* *Invited Paper*